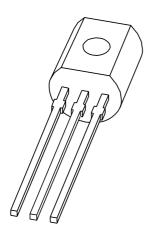
DISCRETE SEMICONDUCTORS

DATA SHEET



BC368 NPN medium power transistor; 20 V, 1 A

Product specification Supersedes data of 2003 Dec 01 2004 Nov 05





NPN medium power transistor; 20 V, 1 A

BC368

FEATURES

• High current.

APPLICATIONS

- Linear voltage regulators
- Low side switch
- Supply line switch for negative voltages
- MOSFET driver
- Audio (pre-) amplifier.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	20	V
Ic	collector current (DC)	_	1	Α
I _{CM}	peak collector current	_	2	Α
h _{FE}	DC current gain	85	375	_

DESCRIPTION

NPN medium power transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	P/	ACKAGE	MARKING CODE	PNP COMPLEMENT	
I THE NOWIBER	PHILIPS	EIAJ	WARKING CODE	PINP COMPLEMENT	
BC368	SOT54	SC-43A	C368	BC369	

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CVMDOL	PINNING		
	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION	
BC368		1	base	
		2	collector	
	1 1 2 MAM259	3	emitter	

ORDERING INFORMATION

TYPE NUMBER		PACKAGE			
		DESCRIPTION	VERSION		
BC368	SC-43A plastic single-ended (through hole) package; 3 leads SOT		SOT54		

NPN medium power transistor; 20 V, 1 A

BC368

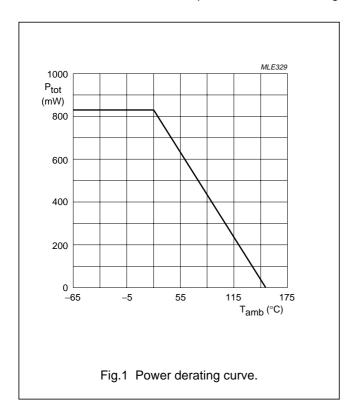
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	32	V
V _{CEO}	collector-emitter voltage	open base	_	20	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	output current (DC)		_	1	mA
I _{CM}	peak collector current		_	2	mA
I _{BM}	peak collector current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; notes 1 and 2	_	0.83	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Notes

- 1. Refer to SOT54 (SC-43A) standard mounting conditions.
- 2. Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated footprint.



NPN medium power transistor; 20 V, 1 A

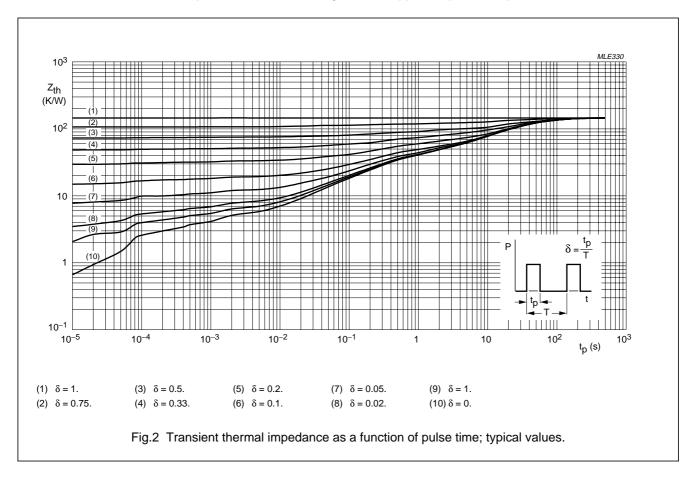
BC368

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C; notes 1 and 2	150	K/W

Notes

- 1. Refer to SOT54 (SC-43A) standard mounting conditions.
- 2. Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated footprint.



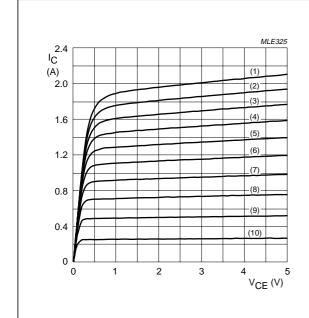
NPN medium power transistor; 20 V, 1 A

BC368

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 25 V; I _E = 0 A	_	_	100	nA
		V _{CB} = 25 V; I _E = 0 A; T _{amb} = 150 °C	_	_	10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 5 mA	50	_	_	
		V _{CE} = 1 V; I _C = 500 mA	85	_	375	
		V _{CE} = 1 V; I _C = 1 mA	60	_	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 1 A; I _B = 100 mA	_	_	500	mV
V_{BE}	base-emitter voltage	$V_{CE} = 10 \text{ V}; I_{C} = 5 \text{ mA}$	_	_	700	mV
		V _{CE} = 1 V; I _C = 1 A	_	_	1	V
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	_	22	_	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 50 mA; f = 100 MHz	40	170	_	MHz



 T_{amb} = 25 °C.

(1) $I_B = 10 \text{ mA}$.

(6) $I_B = 5 \text{ mA}.$

(2) $I_B = 9 \text{ mA}$.

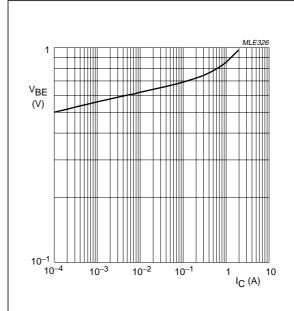
(7) $I_B = 4 \text{ mA}.$

(3) $I_B = 8 \text{ mA}$. (4) $I_B = 7 \text{ mA}$. (8) $I_B = 3 \text{ mA}.$

(5) $I_B = 6 \text{ mA}.$

(9) $I_B = 2 \text{ mA}$. (10) $I_B = 1 \text{ mA}$.

Fig.3 Collector current as a function of collector-emitter voltage; typical values.

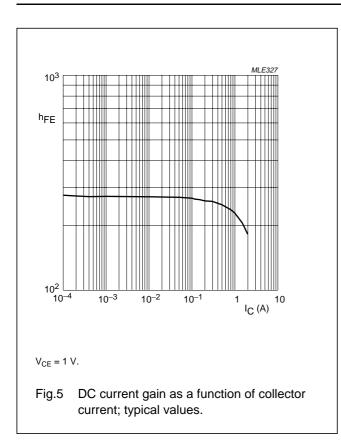


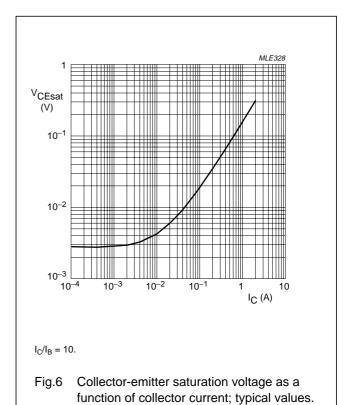
 $V_{CE} = 1 V$.

Fig.4 Base-emitter voltage as function of collector current; typical values.

NPN medium power transistor; 20 V, 1 A

BC368





2004 Nov 05

6

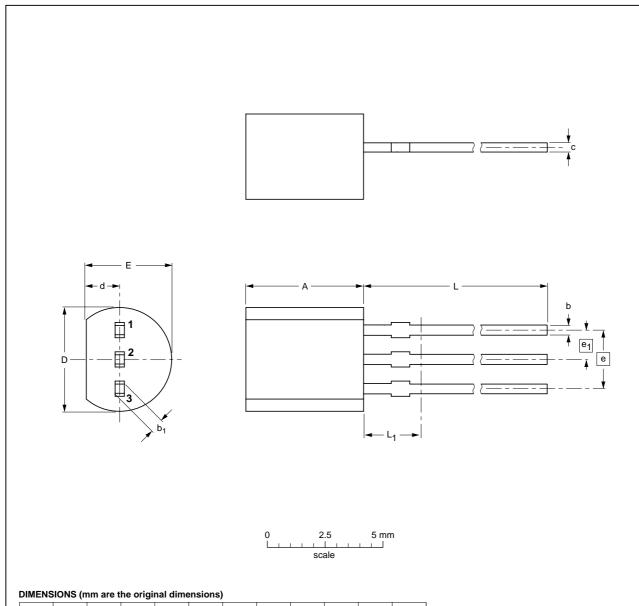
NPN medium power transistor; 20 V, 1 A

BC368

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A			97-02-28 04-06-28	

NPN medium power transistor; 20 V, 1 A

BC368

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
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